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Manufacturers of World Class Discrete Semiconductors

1N3062
1N3063
1N3064

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N3062 Series types are very high speed Silicon Switching Diodes designed for computer and general purpose applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	1N3062	1N3063	1N3064	UNIT
Peak Repetitive Voltage	V_{RRM}	75	75	75	V
Peak Working Reverse Voltage	V_{RWM}	50	50	50	V
Average Forward Current	I_O	75	75	75	mA
Forward Steady-State Current	I_F	115	115	115	mA
Peak Forward Current (Recurrent)	I_{FM}	225	225	225	mA
Peak Forward Surge Current (1.0μs)	I_{FSM}	2000	2000	2000	mA
Power Dissipation	P_D	250	250	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 TO +200		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	V_R=50V		0.1	μA
I_R	V_R=50V, T_A=150°C		100	μA
BV_R	I_R=5.0μA	75		V
V_F	I_F=250μA	0.505	0.575	V
V_F	I_F=1.0mA	0.55	0.65	V
V_F	I_F=2.0mA	0.61	0.71	V
V_F	I_F=10mA (1N3064)	-	1.0	V
V_F	I_F=10mA (1N3063)	0.7	0.85	V
V_F	I_F=20mA (1N3062)	-	1.0	V
C_T	V_R=0V, f=1.0MHz (1N3062)		1.0	pF
C_T	V_R=0V, f=1.0MHz (1N3063, 1N3064)		2.0	pF
t_{rr}	V_r=6.0V, I_f=10mA, R_L=100Ω (1N3062)		2.0	ns
t_{rr}	V_r=1.0V, I_f=10mA, R_L=100Ω (1N3063, 1N3064)		4.0	ns
RE	f=1.0MHz	45		%
ΔV_F/°C			1.8	mV/°C